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WX048N04KF

Enhancement Mode N-Channel Power MOSFET

TO-263/NMOS/40V/±20V/1.8V/80A/4.8mΩ

Rev0.5

40V, 4.8mΩ, 80A, N-Channel Enhancement MOSFET

1.Features

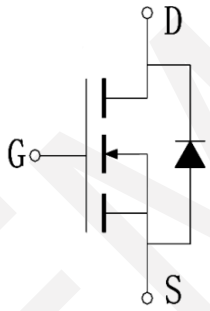
- 40V MOSFET technology
- Low on-state resistance
- Fast switching
- Vgs±20V
- 100% RG Tested
- 100% UIS Tested

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
40V	4.8mΩ @ 10V	80A
	6.4mΩ @ 4.5V	

2.Applications

- Power Switching Application
- Load Switching

TO-263
Pin Description



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WX048N04KF	048N04	TO-263	800	4,800

4.Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	40	V
Gate to Source Voltage	V_{GSS}	±20	V
Drain Current (DC)	I_D	80	A
Drain Current (Pulse), PW≤300μs	I_{DP}	320	A
Total Dissipation	P_D	39	W
Avalanche Energy, Single Pulsed	E_{AS}	217	mJ
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5.Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Case	$R_{\theta JC}$	1.8	℃/W

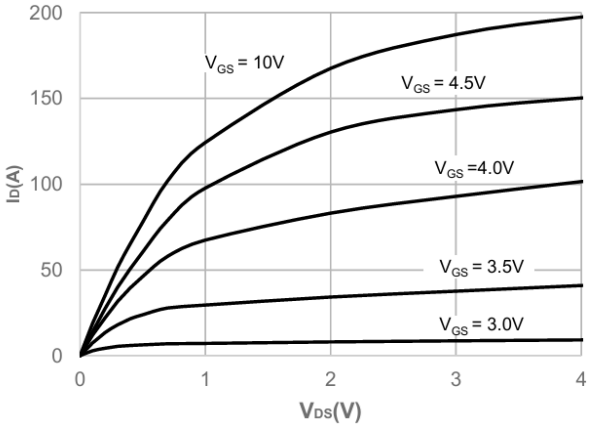
Note 2：When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25℃ (Note 3)

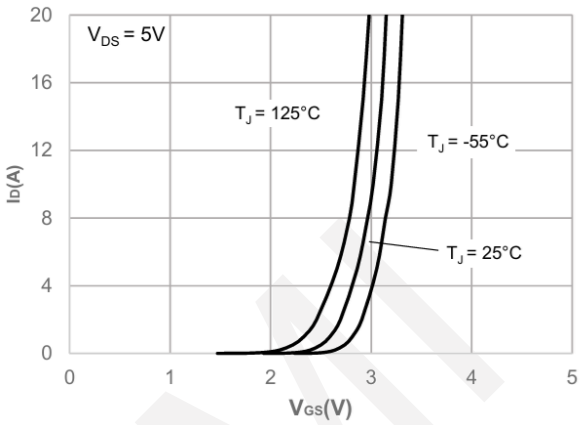
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	40	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} =40V, V_{GS} = 0V	-	-	1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=250μA	1.0	1.8	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	I_D =30A, V_{GS} = 10V	-	4.8	6.0	mΩ
		I_D =20A, V_{GS} = 4.5V		6.4	8.8	mΩ
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=20V, Frequency=1.0MHz	-	3068	-	nF
Output Capacitance	C_{oss}		-	210	-	pF
Reverse Transfer Capacitance	C_{rss}		-	177	-	pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DD} =20V,V_{GS} = 10V, I_D = 30A,R_{GEN} =3Ω	-	11	-	ns
Rise Time	t_r		-	32	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	52	-	ns
Fall Time	t_f		-	13	-	ns
Total Gate Charge	Q_g	V_{DS} =20V, V_{GS} =0 to 10V, I_D =30A	-	59	-	nC
	Q_{gs}		-	12	-	nC
	Q_{gd}		-	12	-	nC
Diode Forward Voltage	V_{FSD}	I_S =30A, V_{GS} = 0	-	-	1.2	V

Note 3：Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

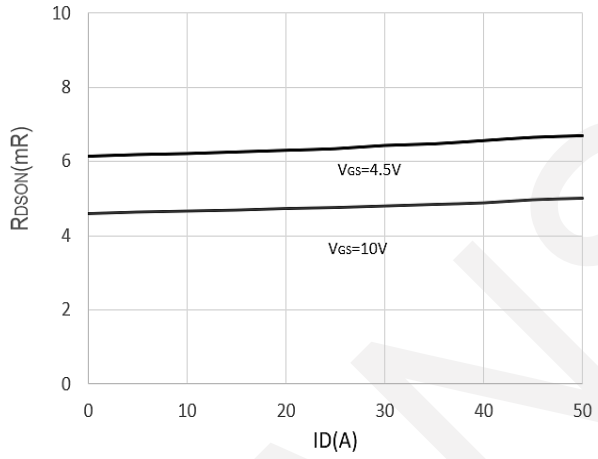
7.Typical electrical and thermal characteristics



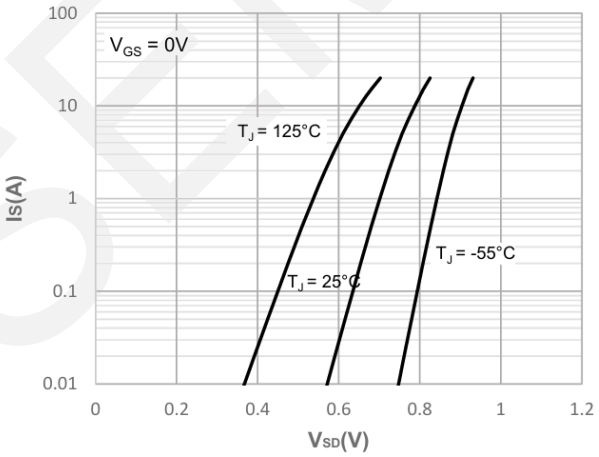
Output Characteristics



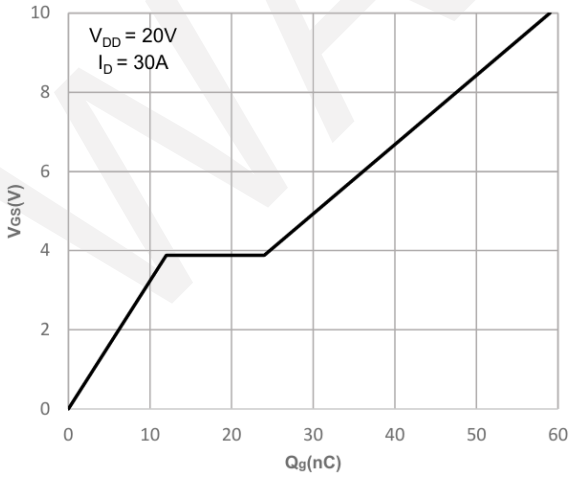
Typical Transfer Characteristics



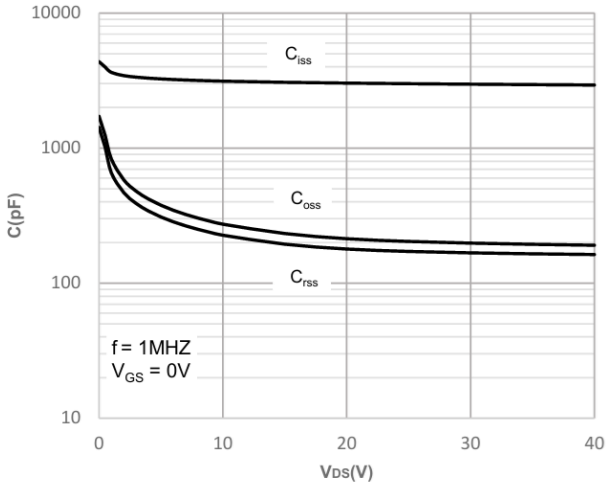
On-resistance vs. Drain Current



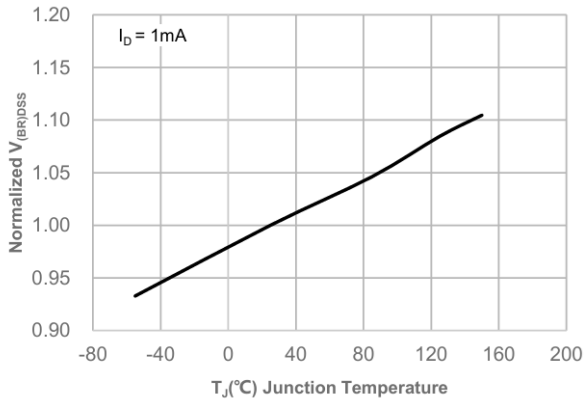
Body Diode Characteristics



Gate Charge Characteristics

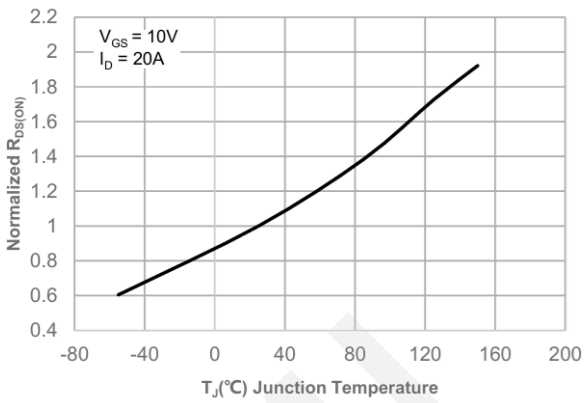


Capacitance Characteristics



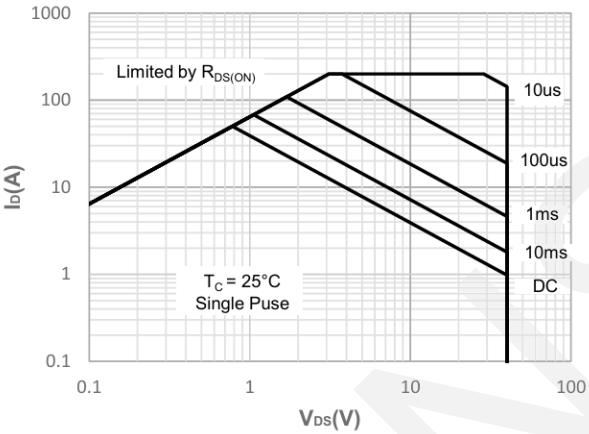
Normalized Breakdown Voltage vs.

Junction Temperature

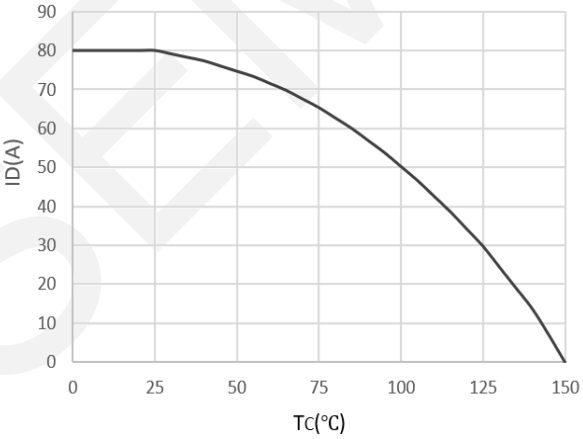


Normalized on Resistance vs.

Junction Temperature

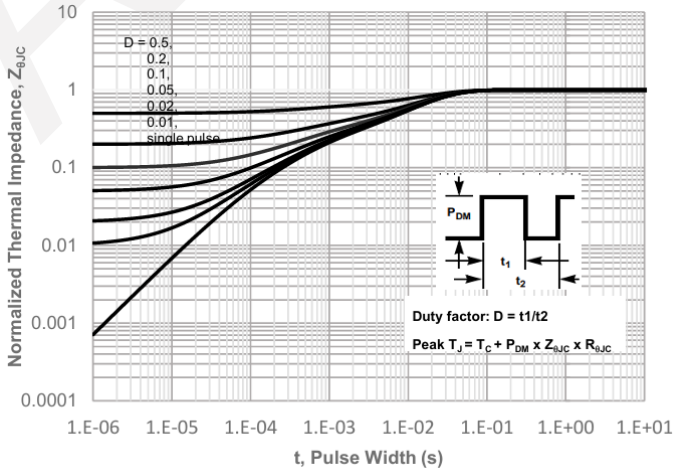


Maximum Safe Operating Area



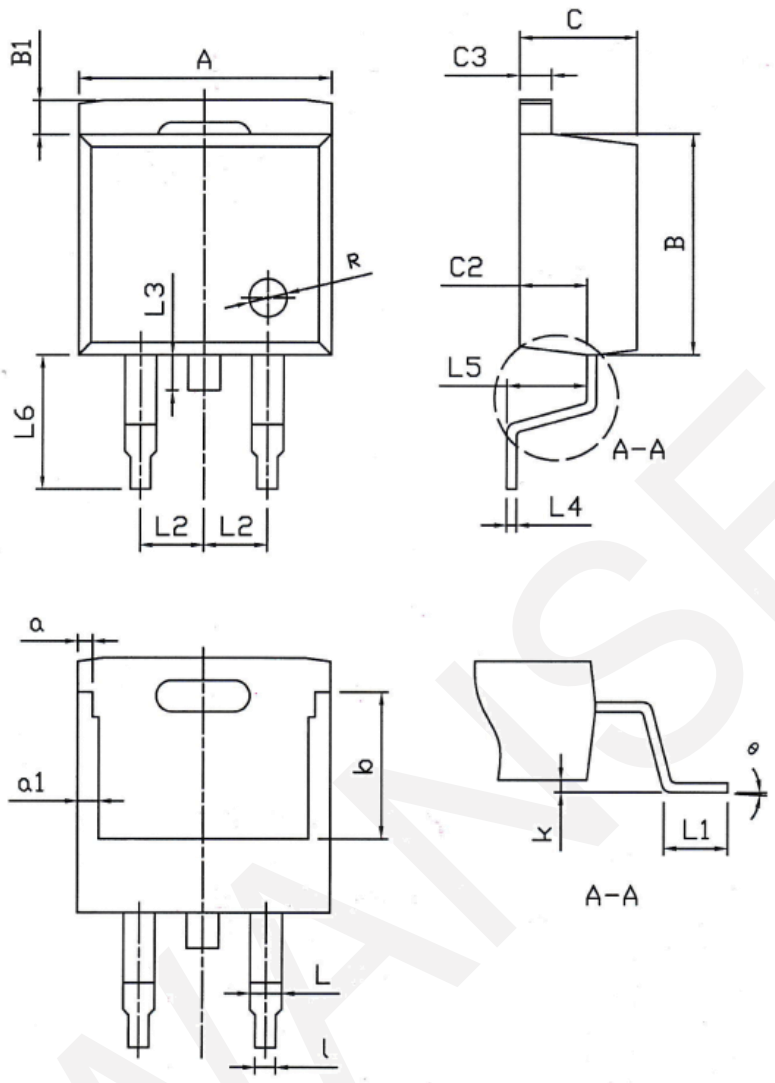
Maximum Continuous Drain Current vs.

Case Temperature



Maximum Effective Transient
Thermal Impedance, Junction-to-Case

8.Package Dimensions



Dimensions In Millimeters			
Symbol	MIN	TYP	MAX
A	10.00	10.20	10.40
B	8.50	8.70	8.90
B1	1.06	1.26	1.46
C	4.49	4.69	4.89
C2	2.54	2.69	2.84
C3	1.17	1.27	1.37
L	1.12	1.27	1.42
L1	2.34	2.54	2.74
L2	-	2.54	-
L3	1.20	1.40	1.60
L4	0.281	0.381	0.481
L5	2.54	2.79	3.04
L6	5.05	5.30	5.55
R	-	1.50	-
a	0.455	0.655	0.855
a1	0.70	0.90	1.10
b	5.648	5.798	5.948
k	0.00	-	0.25
l	0.70	0.81	0.96
θ	0°	-	9°

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